

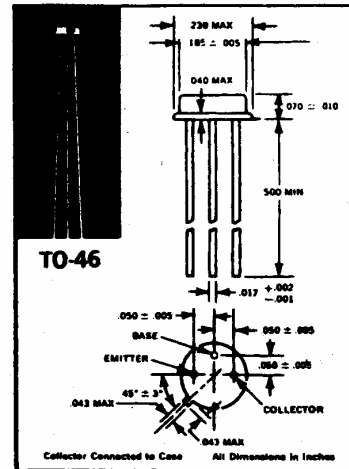
ULTRA LOW $r_{EC}(\text{sat})$ SILICON EPITAXIAL JUNCTION NPN/PNP SWITCHING TRANSISTORS	2N6566 2N6567
---	------------------------------------

GEOMETRY 453, BOTH NPN & PNP

- COMPLEMENTARY TYPES 2N6566(NPN), 2N6567(PNP)
- $r_{EC}(\text{sat})$ 2 Ohms MAX.
- LOW C_{ob}
- LOW LEAKAGE
- HIGH BV_{EBO}

ELECTRICAL DATA: ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	2N6566-2N6567	UNITS
Collector to Emitter Voltage	BV_{CES}	30	Volts
Emitter to Collector Voltage	BV_{ECS}	20	Volts
Collector to Base Voltage	BV_{CBO}	30	Volts
Emitter to Base Voltage	BV_{EBO}	30	Volts
Collector Current	I_C	100	mA
Power Dissipation	P_C	400.	mW
Derating Factor	DF	2.3	mW/°C
Junction Temperature (operating and storage)	T_J	-65°C to +200°C	
Lead Temperature (1/16" ± 1/32" from case)	T_L	240°C for 10 sec.	



ELECTRICAL CHARACTERISTICS: $T_A = 25^\circ\text{C}$ (UNLESS OTHERWISE STATED)

PARAMETER	SYMBOL	CONDITION	2N6566-2N6567			UNITS
			Min.	Typ.	Max.	
Collector To Base Leakage	I_{CBO}	$V_{CB} = V_{CBMAX}$	—	0.2	0.5	nA
Emitter to Base Leakage	I_{EBO}	$V_{EB} = V_{EBMAX}$	—	0.2	0.5	nA
Collector To Base Leakage	I_{CBO}	$V_{CB} = V_{CBMAX}$ (TEMP = 100°C)	—	30	100	nA
Emitter To Base Leakage	I_{EBO}	$V_{EB} = V_{EBMAX}$ (TEMP = 100°C)	—	30	100	nA
Offset Voltage	V_O	$I_B = 1\text{mA}$ $I_E = 0$	—	0.7	1.0	mV
DC Common Collector Forward Current Transfer Ratio	h_{FC}	$V_{EC} = 6\text{V}$ $I_E = 1\text{mA}$	30	—	—	—
High Frequency Current Gain	h_{fe}	$V_{CE} = 6\text{V}$, $I_C = 1\text{mA}$ $f = 1\text{MC}$	3	—	—	—
Inverted Dynamic Saturation Resistance	$r_{EC}(\text{sat})$	$I_e = 1.0\text{mA}$ $I_b = 10\text{mA}$ $f = 1\text{kHz}$	—	1.5	2	Ohms
Collector To Base Capacitance	C_{ob}	$V_{CB} = 6\text{V}$, $I_C = 1\text{mA}$, $f = 159\text{kHz}$	—	8	10	pf
Emitter To Base Capacitance	C_{eb}	$V_{EB} = 6\text{V}$, $I_E = 0$, $f = 159\text{kHz}$	—	5	6	pf

CRYSTALONCS
 2805 Veterans Highway
 Suite 14
 Ronkonkoma, N.Y. 11779